



HPO- 016AP-U-FA1

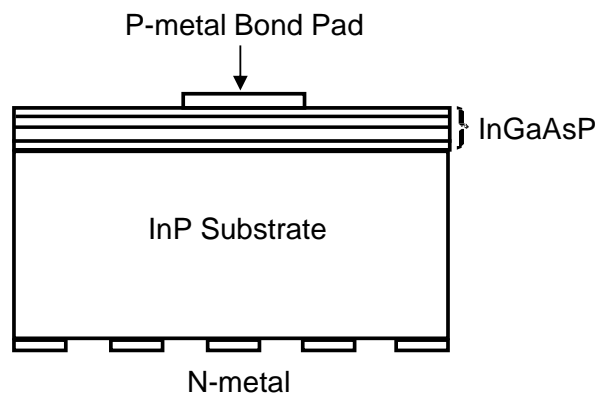
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Chip characteristics:

- **Chip size:** $400 \pm 25 \mu\text{m} \times 400 \pm 25 \mu\text{m}$
- **Chip thickness:** $150 \pm 25 \mu\text{m}$
- **P-bonding pad:** Au pad $\phi 90 \pm 15 \mu\text{m}$
- **Conductive InP-substrate**

Descriptions:

016AP is an near-infrared LED chip made from MOCVD process. 016AP is featured by homogeneous and high light output at top side with superior beam pattern. Excellent performance under sunlight and reliable life-long stability make 016AP ideal for optical sensor applications including analysis of agricultural crops, foods, health and medicine applications.



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Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{F1}	-	0.9	1.0	V	$I_F=20 \text{ mA}$
Reverse Current	I_R	-	-	10.0	μA	$V_R=1.5 \text{ V}$
Peak wavelength	λ_p	1300	-	1350	nm	$I_F=20 \text{ mA}$
Radiant Power	P_o	0.5	-	-	mW	$I_F=20 \text{ mA}$

* P_o is measured on chip form with HPO's tester.